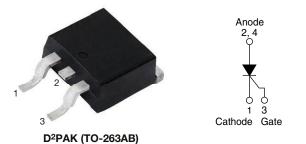


Vishay Semiconductors

Thyristor, Surface Mount, Phase Control SCR, 16 A



PRIMARY CHARACTERISTICS					
I _{T(AV)} 16 A					
V _{DRM} /V _{RRM}	800 V, 1200 V				
V _{TM}	1.25 V				
I _{GT}	45 mA				
TJ	-40 to +125 °C				
Package	D ² PAK (TO-263AB)				
Circuit configuration	Single SCR				

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified according JEDEC[®]-JESD 47

RoHS COMPLIANT HALOGEN

FREE • Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Input rectification (soft start)
- · Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-25TTS...S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS						
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 $\mu m)$ copper	3.5	5.5				
Aluminum IMS, R _{thCA} = 15 °C/W	8.5	13.5	A			
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	16.5	25.0				

Note

• $T_A = 55 \text{ °C}, T_J = 125 \text{ °C}, \text{ footprint } 300 \text{ mm}^2$

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	16	А		
I _{RMS}		25	A		
V _{RRM} /V _{DRM}		800 to 1200	V		
I _{TSM}		350	A		
V _T	16 A, T _J = 25 °C	1.25	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
TJ		-40 to +125	C°		

VOLTAGE RATINGS					
VRRM, MAXIMUM PEAK VDRM, MAXIMUM PEAK IRRM/IDRM, PART NUMBER REVERSE VOLTAGE DIRECT VOLTAGE AT 125 °C V V mA					
VS-25TTS08S-M3	800	800	10		
VS-25TTS12S-M3	1200	1200	10		

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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	OL TEST CONDITIONS		VALUES		UNITS
FARAMETER	STMDUL	IES	T CONDITIONS	TYP.	MAX.	UNITS
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° c	onduction half sine wave	1	6	
Maximum RMS on-state current	I _{RMS}			2	25	А
Maximum peak, one-cycle,	I	10 ms sine pulse,	rated V _{RRM} applied	3	00	~
non-repetitive surge current	I _{TSM}	10 ms sine pulse,	no voltage reapplied	3	50	
Maximum I ² t for fusing	l ² t	10 ms sine pulse,	rated V _{RRM} applied	4	50	A ² s
Maximum I-t for fusing	1-1	10 ms sine pulse,	no voltage reapplied	630		A-S
Maximum I²√t for fusing	l²√t	t = 0.1 ms to 10 m	t = 0.1 ms to 10 ms, no voltage reapplied		00	A²√s
Maximum on-state voltage drop	V _{TM}	16 A, T _J = 25 °C		1.	25	V
On-state slope resistance	r _t	T _{.1} = 125 °C		12	2.0	mΩ
Threshold voltage	V _{T(TO)}	1) = 125 0		1	.0	V
Maximum reverse and direct leakage current	I _{BM} /I _{DM}	T _J = 25 °C	$V_{\rm B}$ = rated $V_{\rm BBM}/V_{\rm DBM}$	0	.5	
Maximum reverse and direct leakage current	'RM/ 'DM	T _J = 125 °C	VR = Tated VRRM/ VDRM	1	0	
Holding current	Ι _Η	VS-25TTS08, VS-25TTS12	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C	-	150	mA
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$		2	00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to 80 \%, } V_{DRM} = R_g - k = open$		5	00	V/µs
Maximum rate of rise of turned-on current	dl/dt			1	50	A/µs

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak gate power	P _{GM}		8.0	W		
Maximum average gate power	P _{G(AV)}		2.0	vv		
Maximum peak positive gate current	+ I _{GM}		1.5	А		
Maximum peak negative gate voltage	- V _{GM}		10	V		
		Anode supply = 6 V, resistive load, $T_J = -10 \ ^{\circ}C$	60			
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	45	mA		
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	20	1		
		Anode supply = 6 V, resistive load, $T_J = -10 \ ^{\circ}C$	2.5			
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	2.0	V		
		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	v		
Maximum DC gate voltage not to trigger	V _{GD}	T 105 °C V reteductue	0.25			
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = rated value	2.0	mA		

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9			
Typical reverse recovery time	t _{rr}	T.I = 125 °C	4	μs		
Typical turn-off time	tq	1j=123 C	110			



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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.1	°C/W		
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		40	C/W		
Approvimate weight			2	g		
Approximate weight			0.07	oz.		
Marking davias		Case style D ² PAK (TO-263AB)	25TT	S08S		
Marking device		Case sigle D-PAR (TO-203AD)	25TTS12S			

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μ m] copper 40 °C/W.

For recommended footprint and soldering techniques refer to application note #AN-994

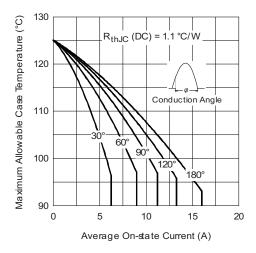


Fig. 1 - Current Rating Characteristics

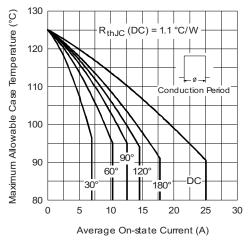


Fig. 2 - Current Rating Characteristics

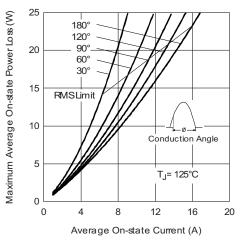


Fig. 3 - On-State Power Loss Characteristics

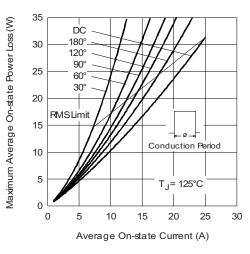


Fig. 4 - On-State Power Loss Characteristics

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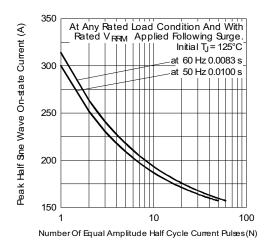


Fig. 5 - Maximum Non-Repetitive Surge Current

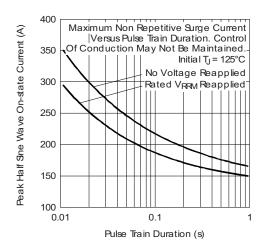


Fig. 6 - Maximum Non-Repetitive Surge Current

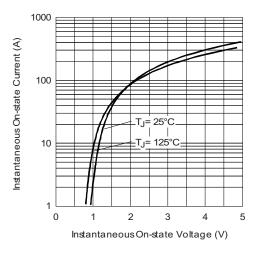


Fig. 7 - On-State Voltage Drop Characteristics



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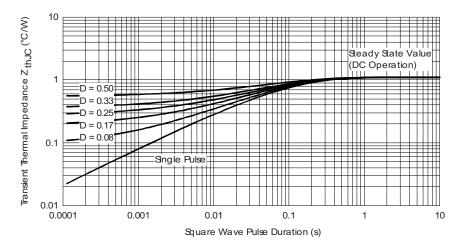


Fig. 8 - Gate Characteristics

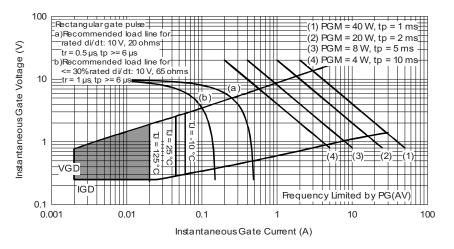
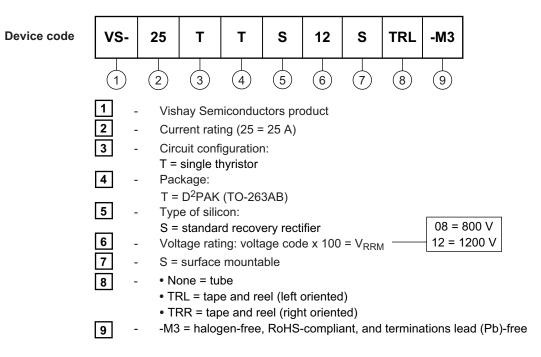


Fig. 9 - Thermal Impedance ZthJC Characteristics



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ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-25TTS08S-M3	50	Antistatic plastic tubes				
VS-25TTS08STRL-M3	800	13" diameter plastic tape and reel				
VS-25TTS08STRR-M3	800	13" diameter plastic tape and reel				
VS-25TTS12S-M3	50	Antistatic plastic tubes				
VS-25TTS12STRL-M3	800	13" diameter plastic tape and reel				
VS-25TTS12STRR-M3	800	13" diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96164			
Part marking information	www.vishay.com/doc?95444			
Packaging information	www.vishay.com/doc?96424			

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D²PAK

DIMENSIONS in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010 BSC		
L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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